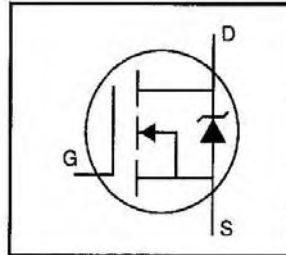


# IRLR014PbF IRLU014PbF

## HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Surface Mount (IRLR014)
- Straight Lead (IRLU014)
- Available in Tape & Reel
- Logic-Level Gate Drive
- RDS(on) Specified at VGS=4V & 5V
- Fast Switching
- Lead-Free

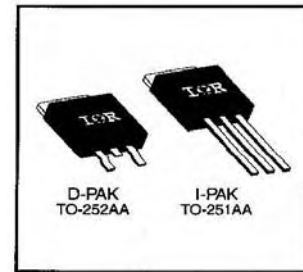


$V_{DSS} = 60V$
$R_{DS(on)} = 0.20\Omega$
$I_D = 7.7A$

### Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	7.7	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 5.0 V$	4.9	
$I_{DM}$	Pulsed Drain Current ①	31	
$P_D @ T_C = 25^\circ C$	Power Dissipation	25	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	2.5	
	Linear Derating Factor	0.20	W/°C
	Linear Derating Factor (PCB Mount)**	0.020	
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$E_{AS}$	Single Pulse Avalanche Energy ②	47	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	260 (1.6mm from case)	

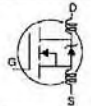
### Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	5.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

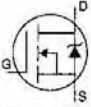
\*\* When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.073	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.20	$\Omega$	$V_{GS}=5.0V, I_D=4.6A$ ④
		—	—	0.28		$V_{GS}=4.0V, I_D=3.9A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$g_{fs}$	Forward Transconductance	3.4	—	—	S	$V_{DS}=25V, I_D=4.6A$ ④
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS}=60V, V_{GS}=0V$
		—	—	250		$V_{DS}=48V, V_{GS}=0V, T_J=125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-10V$
$Q_g$	Total Gate Charge	—	—	8.4	nC	$I_D=10A$
$Q_{gs}$	Gate-to-Source Charge	—	—	3.5		$V_{DS}=48V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	6.0		$V_{GS}=5.0V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	9.3	—	ns	$V_{DD}=30V$
$t_r$	Rise Time	—	110	—		$I_D=10A$
$t_{d(off)}$	Turn-Off Delay Time	—	17	—		$R_G=12\Omega$
$t_f$	Fall Time	—	26	—		$R_D=2.8\Omega$ See Figure 10 ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	400	—	pF	$V_{GS}=0V$
$C_{oss}$	Output Capacitance	—	170	—		$V_{DS}=25V$
$C_{rss}$	Reverse Transfer Capacitance	—	42	—		$f=1.0\text{MHz}$ See Figure 5

## Source-Drain Ratings and Characteristics

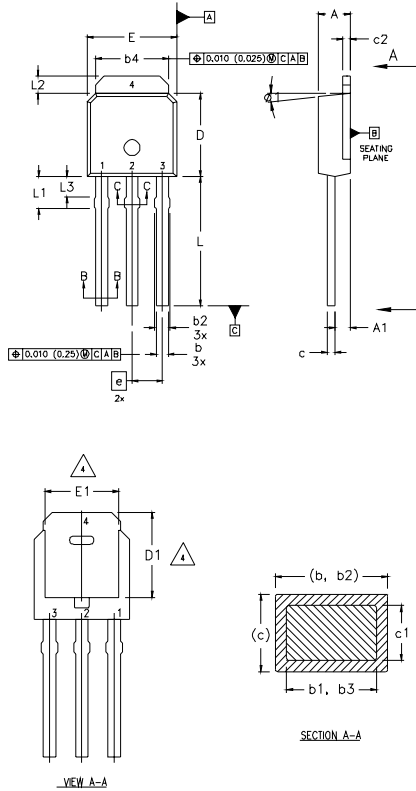
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	7.7	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	31		
$V_{SD}$	Diode Forward Voltage	—	—	1.6	V	$T_J=25^\circ\text{C}, I_S=7.7A, V_{GS}=0V$ ④
$t_{rr}$	Reverse Recovery Time	—	65	130	ns	$T_J=25^\circ\text{C}, I_F=10A$
$Q_{rr}$	Reverse Recovery Charge	—	0.33	0.65	$\mu\text{C}$	$di/dt=100A/\mu\text{s}$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ②  $V_{DD}=25V$ , starting  $T_J=25^\circ\text{C}$ ,  $L=924\mu\text{H}$ ,  $R_G=25\Omega$ ,  $I_{AS}=7.7A$  (See Figure 12)
- ③  $I_{SD}\leq 10A$ ,  $di/dt\leq 90A/\mu\text{s}$ ,  $V_{DD}\leq V_{(BR)DSS}$ ,  $T_J\leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

**LEAD ASSIGNMENTS**

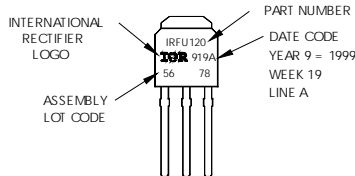
**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.246	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
a1	0'	15'	0'	15'	

## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120 WITH ASSEMBLY LOT CODE 5678 ASSEMBLED ON WW19, 1999 IN THE ASSEMBLY LINE "A"  
**Note:** "P" in assembly line position indicates "Lead-Free"



**OR**

